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RF Power MOSFET Transistor 2 W, 500 - 1000 MHz, 28 V

Features

- N-Channel enhancement mode device
- DMOS structure
- Lower capacitances for broadband operation
- Common source configuration
- Lower noise floor
- Applications
 Broadband linear operation
 500 MHz to 1400 MHz
- RoHS Compliant

Absolute Maximum Ratings @ 25°C

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V _{DS}	65	V
Gate-Source Voltage	V _{GS}	20	V
Drain-Source Current	I _{DS}	0.7	А
Power Dissipation	PD	8	W
Junction Temperature	TJ	200	°C
Storage Temperature	T _{STG}	-55 to +150	°C
Thermal Resistance	θ _{JC}	21.8	°C/W

Typical Device Impedance

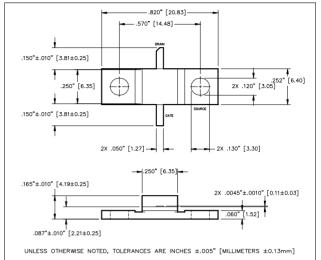
F (MHz)	Z _{IN} (Ω)	Z _{LOAD} (Ω)		
500	10.0 - j41.5	40.0 +j53.0		
1000	4.2 - j12.0	11.85 + j33.0		
1400	3.5 - j1.0 7.5 + j23.3			
V_{DD} = 28V, I_{DQ} = 25mA, P_{OUT} = 2.0 W				

 Z_{IN} is the series equivalent input impedance of the device from gate to source.

 Z_{LOAD} is the optimum series equivalent load impedance as measured from drain to ground.

Electrical Characteristics @ 25°C

Package Outline



LETTER	LETTER MILLIMETERS DIM. MIN MAX		INCHES		
DIM.			MIN	MAX	
А	20.70	20.96	.815	.825	
В	14.35	14.61	.565	.575	
С	13.72	14.22	.540	.560	
D	6.27	6.53	.247	.257	
E	6.22	6.48	.245	.255	
F	6.22	6.48	.245	.255	
G	1.14	1.40	.045	.055	
Н	2.92	3.18	.115	.125	
J	1.40	1.65	.055	.065	
К	1.96	2.46	.077	.097	
L	3.61	4.37	.142	.172	
М	.08	.15	.003	.006	

Parameter	Symbol	Min	Мах	Units	Test Conditions
Drain-Source Breakdown Voltage	BV _{DSS}	65	-	V	V_{GS} = 0.0 V , I_{DS} = 1.0 mA
Drain-Source Leakage Current	I _{DSS}	-	0.5	mA	V_{GS} = 28.0 V , V_{GS} = 0.0 V
Gate-Source Leakage Current	I _{GSS}	-	0.5	μA	V_{GS} = 20.0 V , V_{DS} = 0.0 V
Gate Threshold Voltage	V _{GS(TH)}	2.0	6.0	V	V _{DS} = 10.0 V , I _{DS} = 5.0 mA
Forward Transconductance	G _M	40	-	mS	V_{DS} = 28.0 V , I_{DS} = 50.0 mA , ΔV_{GS} = 1.0V, 80 μs Pulse
Input Capacitance	CISS	-	3.5	pF	V _{DS} = 28.0 V , F = 1.0 MHz
Output Capacitance	C _{OSS}	-	3.75	pF	V _{DS} = 28.0 V , F = 1.0 MHz
Reverse Capacitance	C _{RSS}	-	1.2	pF	V _{DS} = 28.0 V , F = 1.0 MHz
Power Gain	G₽	10	-	dB	V_{DD} = 28.0 V, I_{DQ} = 25 mA, P_{OUT} = 2.0 W F =1.0 GHz
Drain Efficiency	ŋ₀	40	-	%	V_{DD} = 28.0 V, I _{DQ} = 25 mA, P _{OUT} = 2.0 W F =1.0 GHz
Load Mismatch Tolerance	VSWR-T	-	20:1	-	V_{DD} = 28.0 V, I_{DQ} = 25 mA, P_{OUT} = 2.0 W F =1.0 GHz

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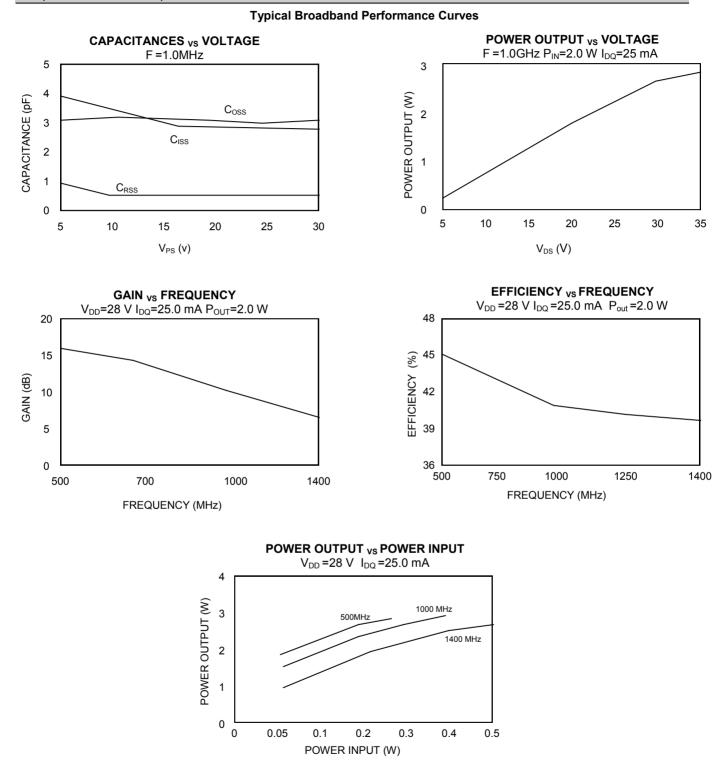
Rev. V1



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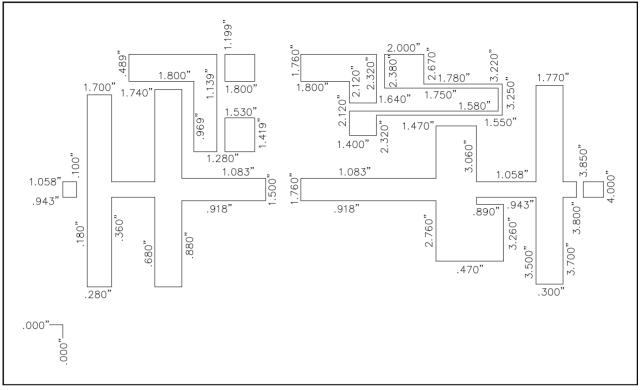
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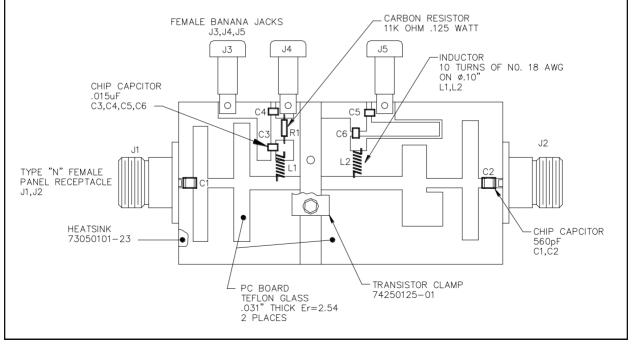
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TEST FIXTURE CIRCUIT DIMENSIONS



TEST FIXTURE ASSEMBLY



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Rev. V1

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